PAGE 02

S/N 09/652,430

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Biswajit Sur et al.

Examiner: Andy Huynh

Serial No.:

09/652,430

Group Art Unit; 2818

Filed:

August 31, 2000

Docket No.: 884.319US1

Title:

ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL

INTERPACE (As Amended)

Customer No: 21186

Assignes: Intel Corporation

DECLARATION UNDER 37 C.F.R. § 1.131

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

This declaration is submitted under 37 C.F.R. §1.131 prior to any final rejection of U. S. Patent Application Serial Number 09/652,430 to establish invention of the subject matter of the rejected claims prior to September 30, 1999.

- I, Biswajit Sur, do hereby declare;
- I have been employed by Intel Corporation from prior to September 30, 1999 until the l. present. My current job title is Manager of Assembly and Packaging.
- 2. I am a co-inventor of the inventive subject matter of the present application as described illustrated, and claimed therein.
- 3. Prior to September 30, 1999, the inventive subject matter that is described, illustrated, and claimed in corresponding claims of the present application was completed in the United States as evidenced by the following:
 - Prior to September 30, 1999, having earlier conceived the claimed subject matter in the United States with the co-inventors, I personally generated an Invention Disclosure, a copy of which is attached hereto as Exhibit A (7 pages). The "Invention Date" deleted from page 1 of Exhibit A is prior to September 30, 1999. Other sensitive information has been blocked out from Exhibit A.

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DECLARATION UNDER 37 C.F.R. § 1.331 Serial Number: 09/652,430

Piting Date: August 31, 2000

Pare : Db; 884,319US1 (INTL)

Title: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERPACE (As Amended)

- Figure 1 of Exhibit A illustrates conceptually an integrated circuit die attached to Ъ. an organic land grid array (OLGA) substrate with solder bumps. An integrated heat spreader (IHS) is attached to the back side of the die using a low melting point solderbased thermally conductive interface material, also referred to variously in Exhibit A as "thermal interface material", a "thermal attach", and a "thermal interface".
- Prior to September 30, 1999, I was personally involved in the construction of prototype integrated circuit packages utilizing a solder thermal interface technique, as described in Exhibit A. My responsibilities included the design, selection, and procurement of low melting point solder materials/alloys; plating of solderable metal layers on lids; defining a suitable and manufacturable process to form a reliable thermal interface between the integrated circuit device and the lid compatible with the package and circuitry; building and testing of prototypes; and analyzing the results.
- The results of four different low melting point solder alloys tested are shown in d. Table 2 of Exhibit A. These solder alloys (Cu_2, Cu_281, Cu_290, and Cu_4) correspond to the four solder alloys identified by the corresponding Indalloy numbers in Table I on page 9 of the present application.
- Prior to September 30, 1999, I generated a Powerpoint presentation entitled "Results from Experiments on Solder Alloy as Thermal Interface Material", which summarizes the results of experiments using a low melting point solder alloy as a thermally conductive interface material. Pages 1-4 of this Powerpoint file are attached hereto as Exhibit B (4 pages). The date deleted from the footer of Exhibit B is prior to September 30, 1999. Other sensitive information has been blocked out from Exhibit B.
- Exhibit B. page 2, describes forming successive layers of titanium (Ti), nickelf. vanadium (Ni/V), and gold (Au) on the backside of a die; coating two different types of heat spreaders, one made of aluminum-silicon-carbide (AIS:C) and the other made of

PAGE 84

DECLARATION UNDER 37 C FR. § 1.131 Serial Number: 09/652,430

Pare Dia: 884.3 (9US) (INTE

Fibrig Date: August 31, 2000
Title: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERFACE (As Amended) Assignee: fauet Corporation

copper (Cu), with nickel (Ni); and testing four different low melting point solder materials identified by Indalloy Numbers 281, 290, 2, and 4. Again, these solder alloys correspond to the four solder alloys identified by corresponding Indalloy numbers in Table 1 on page 9 of the present application, and they also correspond to the four solder alloys appearing in Table 2 of Exhibit A.

- Exhibit B, page 3, describes various assembly details in forming prototype g. integrated circuit packages incorporating a low melting point solder alloy as a thermally conductive interface material.
- Exhibit B, page 4, illustrates a graph of thermal resistance measurements for eig: h. different prototype integrated circuit packages incorporating a low melting point solder alloy as a thermally conductive interface material.
- When I firstshed testing and evaluating the prototype integrated circuit packages believed that they worked satisfactorily for their intended purpose, i.e. to transfer heat from an integrated circuit through a low melting point solder-based thermal interface material to a lid or integrated heat spreader.
- 4. I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements are made with the knowledge that willful false statements and the like are punishabl? by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of this application or any patent issuing thereon.

Biswajit Sur

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Page Die: 684.319US1 (DIT) DECLARATION UNDER 37 C.F.R. § 1.131 Serial Number: 09/632,430
Filing Date: August 3), 1000
Title: ELECTRONIC ASSEMBLY COMPRISING SOLDERABLE THERMAL INTERPACE (As Annobad) Assignee, Intel Corporation

BISWAJIT SUR ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. Attorneys for Intel Corporation

Walter W. Nielsen Reg. No. 25,539

CERTIFICATS UNDER 30 CPR 1.5; The undersigned hereby certifies that this correspondence is being deposited with the United States Posts Service with sufficient postage as first class read, in an envelope addressed for Commissioner of Patents, P.O. Box 1450, Alexandria, VA 223 1450, on this _______ day of September 2003.

Signature No roc

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INVENTION DISCLOSURE, Rev 1 Located at: http://legal.intel.com

Fill out the below and follow the instructions:

1. Cald of the invention:

Semiconductor Process: device and integration Semiconductor Process + Equipment: thin films Semiconductor Process + Equipment: stab/litho

Circuit Design

Test CON (GRM) RECEIVED .

X Packaging Boarde/Cartridge

Autometion Other PATENT DATABASE GROUP INTEL LEGAL TEAM

2. Concine Title of invention:

A low-mailing soft solder thermal interface technique for organic file-chip packages to dissipate a high power density.

Brief Description of invention (please tree privates) and font #10 or larger. Write the
Key Elements of the Invention):

The invertion is: Technique of forming a high performance thermal interface using a low-meiting soft solder alloy between the Ripped die and the integrated heat apreciar in an organic Rip-only package (also known as C4 OLGA). The proposed thermal interface will have a capability of dissipating a large power density. Quantitatively, this interface will provide a thermal resistance that is (at least) takes as good as compared to the best available polyments thermal interface of today. The added advantage of this specific low-meiting soft animal approach is that it is not expected to negatively degrade the package reliability.

Descriptions

Problem: Today's best available polymeric thermal interface materials (aliver filed or sluminum filed) are capable of delivering a normalized thermal resistance of 0.4°C-cm²/W for a large die, and a target of 0.50°C-cm²/W is considered to be a stretch goal.

moistions: In order to break the thermal resistance barrier a high performance thermal interface is required. An inherest high thermal conductivity, and a proper bondline control are the two elements in achieving such a high performance interface. Using the proposed technique of this disclosure a low melting point soft solds alloy of high thermal agnitutivity can be used as the thermal treatable proper adhesion and bondline control of the interface are be achieved by a proper selection of solderable interfaces, and process conditions.

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PAGE 07

THE REPORT OF CONTRACT PROPERTY PROPERTY.

4. Inventor(s):

Name: Blown It Bur

Phone:

406-765-2736 Offsenship: India Group Name: PD

Division Name: ATD_ PTD___CTM___GR___ STID___OQN_

TCAD___ BUTD Other?___TCAD

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SAUTO___TCAD__

Jest Worldman

Phoma: (408) 553-60b1 Citizenanip:

USA Group Name: <u>01 (maiert</u> Division Nerral; ATO____

PTD__CIM_X_CR__ STTD__OQN__ SMTD_ __TOAD___ OH-T_

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Fac

400-053-0063 Supervisor Name: Kevin J. Haley **BUM Presenter:** Steve Smith

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480-652-4001

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Supervisor Phone: 408-785-4062

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M/S

Supervisor M/R:

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SC12-504

MS

RN2-35

Empl.

Supervisor Phone: (408) 785-9890 Inventor Signature: Supervisor M/3:

RN2-35

e

(PROVIDE SAME INFORMATION AS ABOVE FOR EACH ADDITIONAL INVENTOR)

HAVE YOUR SUPERVISOR READ, DATE AND SIGN COMPLETED FORM (use first inventor's 5. supervisor if multiple inventors)

DATE:

SUPERVISOR NAME:

BY THIS SIGNING, I (SUPERVISOR) ACKNOWLEDGE THAT I HAVE READ AND UNDERSTAND THE DISCLOSURE, AND RECOMMEND THAT THE HONORARUM BE PAID.

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PAGE 09

HAVE YOUR SUPERVISOR PEAD, DATE AND SIGN CONFLICTED PORM (see that inventor's improvious & mediate inventory)

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PAGE 10

THE ROLL COLLEGE PRODUCT A TUNE

- Has subject matter of present disclosure been disclosed or will it be disclosed outside intel?

 Wees, explain and give date:

 No. But outsides can determine the technique by cross-sectioning a package. The surflest implementation of this technique in a package can be (Give expected tape out data if applicable):
- Has the subject matter of present disclosure been published or will it be published outside of Not planned currently. Intel? If yes, explain and give date:
- Here a product using or manufactured using the present disclosure been sold or offered for sale? If you, explain and give date: If successful, will be used in future products. Earliest
- Has this invention been conceived, or constructed during accomplishment of a government or third party contract? If you, give contract name and number:
- 10. Explain the problem being addressed by the invention:

This invention addresses the problem of:

Today's best available polymeric thermal interlace materials (aliver filled or sluminum filled) are capable of delivering a normalized thermal resistance of 0,4°C-cm²AV for a large die.

Moreover, many polymeric meterials also produce inherent process artifacts, such as, reain separation, out-geneing, spreader to die delamination, pump-out, etc.

11. Explain surrent state of the art (Le, how the problem is acreed today):

Property the problem described above is enhad by:

A stretch goal of 0.3°C-cmfAV is anticipated today using a polymeric material as thermal interlace of a large die, and any further improvement is essured not activisable.

12. Explain suchnical advantages of the invention over ourrent state of the art.

The technical advantage of this invention is:

The proposed utilization of a highly conductive solder alloy will provide a thermal resistance that is (at least) twice as good as compared to the best available polymeric thermal interface of today. Moreover, the utilization of a soft arider is to temp package and die level stresses low. The choice of a low-melting point is to attain a relatively lower processing temperature and thereby reducing warpage induced atrees in the system. The above two conditions are intended to reduce total stress level in an OLGA2 peckage and thereby enhance the package reliability.

13. a. Is the invention experimentally verified?

Yea.

b. In the invention verified with simulation?

No.

c. If neither a. or b. above, then you can get a patent on the concept, but plants expisin the technical beels to justify that your invention will work (use extra space if necessary):

Please check hext section for experimental verification,

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14. Detailed Description of Invention (<u>try to take only the opens provided</u> with fant \$10 or larger type.

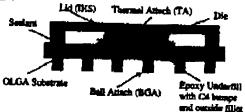


Figure 1. Schematic of an OLGA2 package aboving the buckship of the estached to 1935 with the help of thornal interface material.

As a beckground, on OLGA2 peckage consists of a filp-chip silicon dis attached to an organic land grid array (OLGA) substrate with the help of C4 bumps and an underfill epoxy. An integrated heat opreader (IHSI) is attached to the becketce of the filp-chip die for heat dissipation. A thermaly conductive interface (which is the topic of this disciousre) is used to attach the IHS in the disc. IHS is also attached to the substrate boundary with the help of a sealant for mechanical support. Various components of an OLGA2 package, including the thermal interface / thermal attach are schematically shown in Figure 1.

For forming a low-inelting soft solder thermal interface the following four components are essential: 1) a solderable die backside, 2) a solderable BIS, 3) a subable solder pasts, and 4) a subable process for forming a reliable interface. A procedure for echieving the above four is described in the following.

- 1) Firstly metal layers are required to be deposited on the backside of die (unpolished water) for solderability. The backside of an unpolished water is prepared with a 10 second sputter eith before the metal deposition/sputtering. The metal inver build-up is as follows: a 600Å layer of Ti on backside of the die, followed by a \$500Å layer of NIV, and finelty a 600Å layer of Au. The sputtering parameters are similar to that used for POP C4 BLM processing (C4 BLM TI, C4 BLM NIV), with the addition a gold layer with a P6 backside Au-parameters (except for shorter deposition time). Test waters of 2C112M45 device were used for this test.
- 2) Solderability on IHS can be achieved with a presence of a suitable metal. Two types of IHS materials (Cu and AISIC) were tried in this locability test. A 2 to 5 µm thick Ni layer with shiny finish was loured suitable for analyting solderability on both the material types. Electroless Ni pieting was done in a Niklad 787 bath, using a medium force solution.
- 3) Several different solder alloys (Bi or in alloy) were tried out and found suitable for this thermal interface application. All of them were off-the-shelf materials from Indalloy Corp, and were available in solder pasts form. The solder pasts consists of a no-clean flux vehicle and a 89% loading of the corresponding solder alloy. The solder compositions and relevant properties are given in the following Table 1.

Table 1. Compositions and relevant properties of the solder alloys used in this experiment.

Indelicy Number	Composition	Liquidus 	Seithe.	Thermal Conductivity
201	50 EI / 40 An.	186	136	
256	W/ M/3An	3	143	73
	10 11/15 Th/ FAE	154	140	4
	100 in	1/7		

4) During assembly process the solder pasts is first applied at backgide of die, and then the sealant meterial is dispensed on the pastage boundary. The IHS is then placed, and IHS spring is attached to apply a 3 to 5 be of force. The units in a FOL carrier are then reliowed in N2 environment incide a horizontal BTU furnice for forming the solder joints. During reflow operation of each alloy, the maximum zone temperature in the furnice was maintained as fliquidus + 30°C' and the time above liquidus was -60 accs. Post solder join the assistant was cured in a conventional vertical even.

Drawings (use as many pages as needed) (PLEASE DO NOT MAKE COLOR DRAWINGS)

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HATER COMBINED ATTACK

16. Key Supporting Date (1 page limit on separate page):

The experimental teasibility of this technique is shown in the following figures. The thermal resistance data from 4 alloys were referred to by their numbers and by the type of apreadate (for example, Cu_2 means Cu apreadar with indelloys?) combination). Only the data for Cu IHS is demonstrated here.

Figure 2. Comparison of the rami interface resistance (*C-cm*/W) between all the alloys tested and the present plan of record material. Data shows are for the center sensor (RTD3) for a 2C11ZL die (884:204 mile)

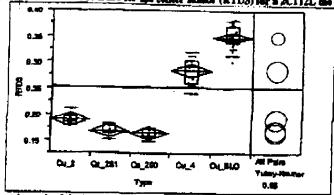
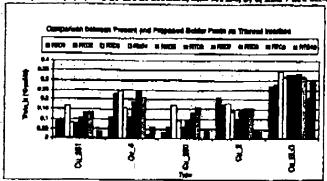


Table 2. Mean and standard devictions of thermal resistance at dis contor for all legs tested.

libers and 8	d Devisions	•	-		
Leni	Hymbia	Man	Bel Day	Std Mr Man	
2 بت	7	0.140	0.011	0.004	
Cu_201	,	0.166	9.010	0.004	
[cr⊤sæ	7	0.186	0.00	0.003	
CU_4	7	0.285	Ô.04A	0.010	
(or = = =	<u> </u>	8.349	0.022	0.008	

Figure 3. Theraul resistance for all the temperature scanors for all the lags (only 1 unit per lag shown). RTD3 and 8 are at center, RTD1, 2, 3, and 10 are at corners, and RTD4, 5, 6, and 7 are off-ountered in the dis.



From above figures and table it is clear that the proposed solder thermal interface technique susperformed the present POR interface, both statistically and technically, by a vast margin (Fig. 1 and Table 2). This improvement is noticed uniformly all across the cite, we can be seen for all the sensors (Fig. 3). It is to be also noted that, without any process optimization, this proof of concept test already showed about a 2x improvement in thermal performance.

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EXHIBIT B - Page 1

Results from Experiment on Solder Alloy as Thermal Interface Material

B. Sur, T. Workman

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Build Details

- 2C112L device was used for this investigation
- Metal was sputtered on backside of die (wafer) for solderability
 - Wafers did not have any backside polishing step
- Metal sputtering on backside at D2: 500Å Ti + 3500Å NiN + 600Å Au

AlSiC (CPS) spreaders were coated with

Ni plating

Ni plating (electroless) at a Santa Clara shop

Cu (Shinko) spreaders had POR Ni coating

Four (4) 'off-the-shelf solder pastes used as thermal interface material

Thermal Conductivity (Swim-°C) Solder paste supplier: Indium Corporation of America 5 73 Solidus () 138 45 4 Composition | Liquidus | ္ဌာ 138 43 7 157 80 In / 15 Pb 58 Bi / 42 Sn 97 In / 3 Ag Indalloy Number 281 8

EXHIBIT B - Page 2

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Page 2

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Build Details (Contd.)

IHS Assembly Details:

1) Solder paste manually applied at backside of die

2) Sealant dispensed on package

3) Spreader placed using manual SPM and template

4) IHS springs attached

IHS spring used:

5) Reflowed in chip-join BTU furnace for solder joint of thermal interface

Belt speed:

Temperatures

Environment: 6) Cured EXHIBIT B - Page 3

8. Sur

Fage 3

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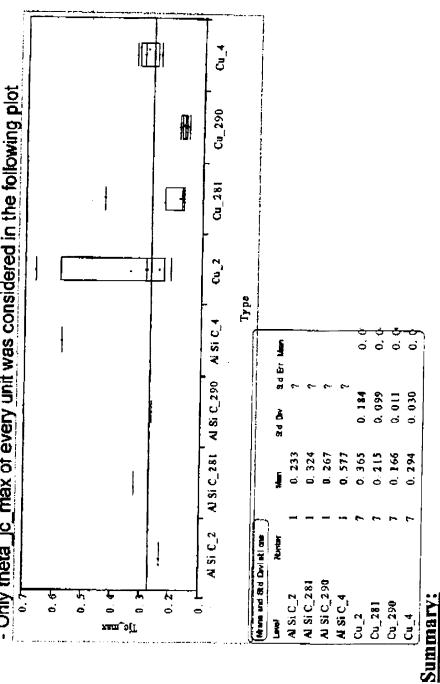
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Tic max for all the Units

- Only theta_jc_max of every unit was considered in the following plot Thermal resistance is normalized for die area (°C-cm²/W)



thermal resistance. For example: $(lot_\mu + 3*lot_\sigma)$ for $(Cu+Alloy290) = 0.199 °C-cm^2/W$ - Results show proof-of-concept that 'solder' thermal interface can give a very low

EXHIBIT B - Page 4

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Page 4

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